

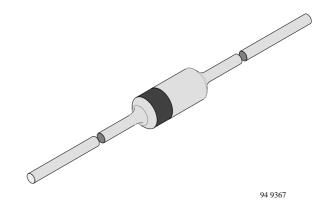
BAT85S

Vishay Semiconductors

Small Signal Schottky Barrier Diode

Features

- Integrated protection ring against static discharge
- Very low forward voltage



Applications

Applications where a very low forward voltage is required

Order Instruction

Туре	Type Differentiation	Ordering Code	Remarks	
BAT85S	V _R = 30 V	BAT85S-TAP	Ammopack	
		BAT85S-TR	Tape and Reel	

Absolute Maximum Ratings

T_i = 25°C

Parameter	Test Conditions	Туре	Symbol	Value	Unit
Reverse voltage			V _R	30	V
Peak forward surge current	t _p ≤ 10 ms		I _{FSM}	5	А
Repetitive peak forward current	t _p ≤1s		I _{FRM}	300	mA
Forward current			۱ _F	200	mA
Average forward current	PCB mounting, I=4 mm; V _{RWM} =25 V, T _{amb} =50 °C		I _{FAV}	200	mA
Junction temperature			Τ _i	125	°C
Storage temperature range			T _{stg}	-65+150	°C

Maximum Thermal Resistance

T_j = 25°C

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	I=4 mm, T _L =constant	R _{thJA}	350	K/W

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Electrical Characteristics

 $T_i = 25^{\circ}C$

Parameter	Test Conditions	Туре	Symbol	Min	Тур	Max	Unit
Forward voltage	I _F =0.1mA		V _F			240	mV
	I _F =1mA		V _F			320	mV
	I _F =10mA		VF			400	mV
	I _F =30mA		V _F			500	mV
	I _F =100mA		VF			800	mV
Reverse current	V _R =25 V		I _R			2	μΑ
Diode capacitance	V _R =1 V, f=1MHz		CD			10	рF

Characteristics ($T_i = 25^{\circ}C$ unless otherwise specified)

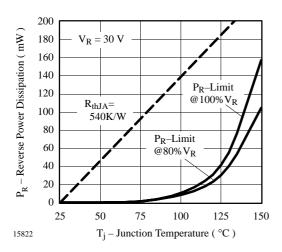


Figure 1. Max. Reverse Power Dissipation vs. Junction Temperature

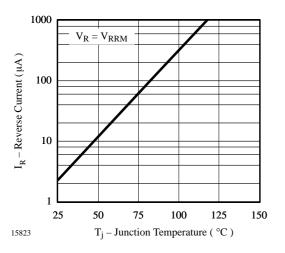
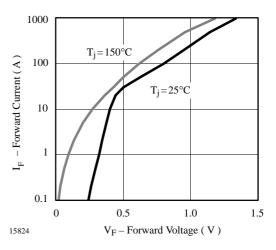
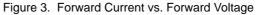


Figure 2. Reverse Current vs. Junction Temperature





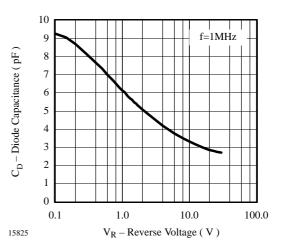
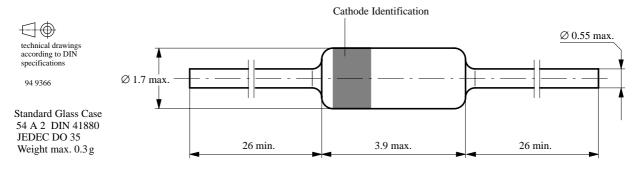


Figure 4. Diode Capacitance vs. Reverse Voltage



BAT85S Vishay Semiconductors

Dimensions in mm



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Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.

2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Visha Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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